

Quad Bidirectional Low-Voltage Logic-Level Translator

General Description

The MAX14611 is a quad bidirectional logic-level translator that provides the level shifting necessary to allow data transfer in a multivoltage system. Externally applied voltages, V_{CC} and V_L , set the logic levels on either side of the device. A low-voltage logic signal present on the V_L side of the device appears as a high-voltage logic signal on the V_{CC} side of the device, and vice-versa.

The device is ideal for I2C bus as well as MDIO bus applications where open-drain operation is often required. The device features a three-state output mode ($\overline{\text{TS}}$). Drive $\overline{\text{TS}}$ high to connect the pullup to the powered I/O port. This allows for continuous, undisrupted I²C operation on the powered side of the device while the level translation function is off. The MAX14611 is a pin-to-pin compatible upgrade to the MAX3378E in the TDFN package.

The MAX14611 features enhanced high-electrostatic-discharge (ESD) protection on all I/OVCC_ ports up to $\pm 6 \text{kV}$ HBM. The device operates over the -40°C to +85°C extended temperature range and is available in 3mm x 3mm, 14-pin TDFN and 4.9mm x 5.1mm, 14-pin TSSOP packages.

Applications

SPI, I²C, and MDIO Level Translation Low-Voltage ASIC Level Translation Portable Electronics Mobile Phones
POS Systems
Telecommunications
Equipment

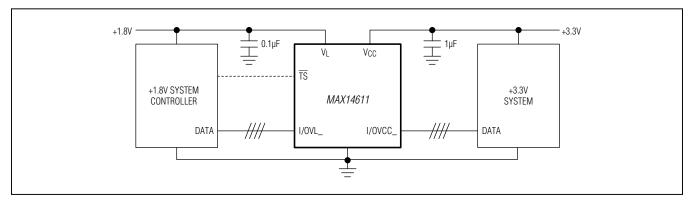
Benefits and Features

- ♦ Improved Interoperability
 - **♦ Meets I²C Specifications**
 - \diamond 10k Ω Internal Pullup Resistor
 - ♦ Pin-to-Pin Compatible with the MAX3377E and the MAX3378E
 - ♦ 0.9V Operation on Low Voltage Supply
- **♦ Robust Logic-Level Translation**

 - ♦ Thermal Short-Circuit Protection
 - **♦ Short to Ground Fault Protection on All Pins**
 - → -40°C to +85°C Operating Temperature Range
- ♦ Increased Design Flexibility
 - **♦ Ultra-Low Supply Current**
 - Pullup Resistor Enabled with a Single Power Supply when TS = High
 - \diamond 10 Ω (max) Transmission Gate FET
 - → Small, 14-Pin, 3.0mm x 3.0mm TDFN Package and 14-Pin, 4.9mm x 5.1mm TSSOP Package

Ordering Information appears at end of data sheet.

Typical Operating Circuit



For related parts and recommended products to use with this part, refer to www.maximintegrated.com/MAX14611.related.

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ABSOLUTE MAXIMUM RATINGS

(All voltages referenced to GND.)		Continuous Power Dissipation ($T_A = +70^{\circ}$	°C)
V _{CC}	0.5V to +6V	TDFN (derate 24.4mW/°C above +70°C	c) 1951.2mW
V _L		TSSOP (derate 10mW/°C above +70°C)796.8mW
TŠ		Operating Temperature Range	40°C to +85°C
I/OVCC	$0.5V \text{ to } (V_{CC} + 0.5V)$	Maximum Junction Temperature	+150°C
I/OVL		Storage Temperature Range	65°C to +150°C
Short-Circuit Duration I/OVL , I/OVCC to 0	, _ ,	Lead Temperature (soldering, 10s)	+300°C
Continuous Current	±50mA	Soldering Temperature (reflow)	+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

PACKAGE THERMAL CHARACTERISTICS (Note 1)

TDFN-EP	TSSOP
Junction-to-Ambient Thermal Resistance (θ_{JA})41°C/W	Junction-to-Ambient Thermal Resistance (θ _{JA})100.4°C/W
Junction-to-Case Thermal Resistance (θ _{JC})8°C/W	Junction-to-Case Thermal Resistance (θ _{JC})30°C/W

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

ELECTRICAL CHARACTERISTICS

 $(V_{CC}=+1.65 V \text{ to } +5.5 V, V_L=0.9 V \text{ to the lesser of } V_{CC}+0.3 V \text{ and } 5 V. T_A=T_J=-40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ Typical values are at $V_{CC}=+3.3 V, V_L=+1.8 V, T_A=+25 ^{\circ}\text{C}, \text{ unless otherwise noted.}$ (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
POWER SUPPLIES							
V _L Supply Range	VL		0.9		5	V	
V _{CC} Supply Range	V _{CC}		1.65		5.5	V	
V _L Supply Current	I _{VL}	$I/OVCC_{-} = V_{CC}, I/OVL_{-} = V_{L}, \overline{TS} = V_{L}$			1	μΑ	
V _{CC} Supply Current	I _{VCC}	$I/OVCC_{-} = V_{CC}$, $I/OVL_{-} = V_{L}$, $\overline{TS} = V_{L}$			35	μΑ	
V Chutdawa Mada Cupalu		TS = GND, I/OVCC = unconnected		0.1	1		
V _{CC} Shutdown Mode Supply Current	ISHDN_VCC	$\overline{TS} = V_{CC}, V_L = GND,$ I/OVCC = unconnected		0.1	1	μΑ	
V 01 11 M 1 0 1	I _{SHDN_} VL	TS = GND		0.1	1		
V _L Shutdown Mode Supply Current		$\overline{TS} = V_L, V_{CC} = GND,$ I/OVL_ = unconnected		0.1	1	μΑ	
I/OVCC_, I/OVL_, TS Leakage Current	ILEAK	$T_A = +25^{\circ}C, \overline{TS} = GND$		0.1	1	μΑ	
TS Input Leakage Current	I _{LEAK_TS}	$T_A = +25^{\circ}C$			1	μΑ	
V _L Shutdown Threshold	V _{TH_VL}			0.3	0.85	V	
V _{CC} Shutdown Threshold	V _{TH_VCC}			0.8	1.35	V	
I/OVL_ Pullup Resistor	R _{VL_PU}			10		kΩ	
I/OVCC_ Pullup Resistor	R _{VCC_PU}			10		kΩ	

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ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +1.65 \text{V to } +5.5 \text{V}, V_L = 0.9 \text{V to the lesser of } V_{CC} + 0.3 \text{V and } 5 \text{V}. T_A = T_J = -40 ^{\circ}\text{C}$ to $+85 ^{\circ}\text{C}$, unless otherwise noted. Typical values are at $V_{CC} = +3.3 \text{V}, V_L = +1.8 \text{V}, T_A = +25 ^{\circ}\text{C}$, unless otherwise noted.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
I/OVL_ to I/OVCC_ DC Resistance	R _{IOVL_IOVCC}	Inferred from V _{OL} measurements		5	10	Ω	
I/OVL_ Input-Voltage High	V _{IHL}		V _L - 0.2			V	
I/OVL_ Input-Voltage Low	V _{ILL}				0.15	V	
I/OVCC_ Input-Voltage High	V _{IHC}		V _{CC} - 0.4			V	
I/OVCC_ Input-Voltage Low	V _{ILC}				0.2	V	
I/OVL_ Output-Voltage High	V _{OHL}	I/OVL_ source current = 10µA	0.7 x V _L			V	
I/OVL_ Output-Voltage Low	V _{OLL}	I/OVL_ sink current = 2mA, V _{I/OVCC} ≤ 50mV			0.4	V	
I/OVCC_ Output-Voltage High	V _{OHC}	I/OVCC_ source current = 10µA	0.7 x V _{CC}			V	
I/OVCC_ Output Voltage Low	V _{OLC}	I/OVCC_ sink current = 2mA, V _{I/OVL} _ ≤ 150mV			0.4	V	
TS Input-Voltage High Threshold	V _{IH}		V _L - 0.2			V	
TS Input-Voltage Low Threshold	V _{IL}	V _L > 1.3V			0.2	V	
Accelerator Pulse Duration		Inferred from timing measurements			30	ns	
V _L Output Accelerator Source		$V_L = 0.9V$		70		Ω	
Impedance		$V_L = 3.3V$	15		52		
V _{CC} Output Accelerator Source		$V_{CC} = 1.65V$		50		Ω	
Impedance		V _{CC} = 5.0V		10		32	
Thermal-Shutdown Threshold		20°C hysteresis		+150		°C	
ESD PROTECTION							
I/OVCC_		Human Body Model, $C_{VCC} = 1\mu F$, $C_{VL} = 0.1\mu F$		±6		kV	
All Other Pins		Human Body Model		±2		kV	

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TIMING CHARACTERISTICS

 $(V_{CC} = +1.65 \text{V to } +5.5 \text{V}, V_L = +0.9 \text{V to the lesser of } V_{CC} + 0.3 \text{V and } 5 \text{V}, \overline{\text{TS}} = V_L, R_L = 1 \text{M}\Omega, C_{VCC} = 1 \mu\text{F}, C_{VL} = 0.1 \mu\text{F}, C_{I/OVCC} = 15 \text{pF}, C_{I/OVCL} = 15 \text{pF}, T_A = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}, \text{ unless otherwise noted.}$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
LOVCC Bigg Time		Push-pull driving (Figure 1)			40	ns	
I/OVCC_ Rise Time	t _{RVCC}	Open-drain driving (Figure 2, Note 5)			100		
LOVOC Fall Time	+	Push-pull driving (Figure 1)			40		
I/OVCC_ Fall Time	tFVCC	Open-drain driving (Figure 2, Note 5)			50	ns	
I/OV/L Dies Time		Push-pull driving (Figure 3)			30		
I/OVL_ Rise Time	t _{RVL}	Open-drain driving (Figure 4, Note 5)			105	ns	
LOVI Fall Time		Push-pull driving (Figure 3)			30		
I/OVL_ Fall Time	t _{FVL}	Open-drain driving (Figure 4, Note 5)			30	ns	
Donas anakina Dalam	I/O _{VL-VCC}	Push-pull driving (Figure 1)			40		
Propagation Delay	I/O _{VL-VCC}	Open-drain driving (Figure 2, Note 5)			150	ns	
Dramagation Daloy	I/O _{VCC-VL}	Push-pull driving (Figure 3)	30		30	ns	
Propagation Delay	I/O _{VCC-VL}	Open-drain driving (Figure 4, Note 5)		10			
Channel-to-Channel Skew		Input rise time/fall time < 6ns, push-pull driving			20		
	tskew tskew	Input rise time/fall time < 6ns, open-drain driving			50	- ns	
Maying un Data Data		Push-pull operation			20	Mbas	
Maximum Data Rate		Open-drain operation (Notes 5, 6)			6	Mbps	

- **Note 2:** All units are 100% production tested at T_A = +25°C. Specifications over operating temperature range are guaranteed by design.
- Note 3: V_L must be less than or equal to V_{CC} during normal operation. However, V_L can be greater than V_{CC} during startup and shutdown conditions.
- Note 4: All timing is 10% to 90% for rise time and 90% to 10% for fall time.
- Note 5: Not production tested; guaranteed by design.
- Note 6: Requires the external pullup resistor.

Quad Bidirectional Low-Voltage Logic-Level Translator

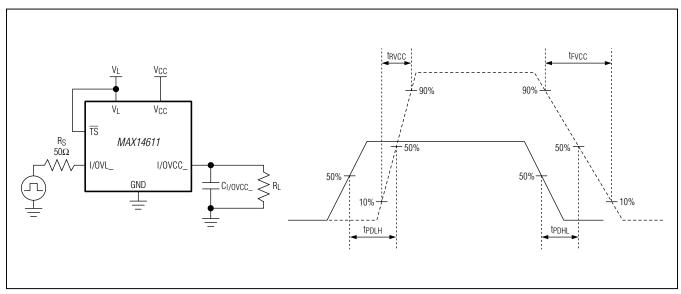


Figure 1. Push-Pull Driving I/OVL_

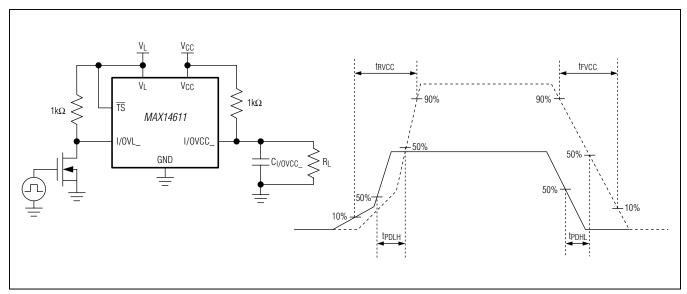


Figure 2. Open-Drain Driving I/OVL_

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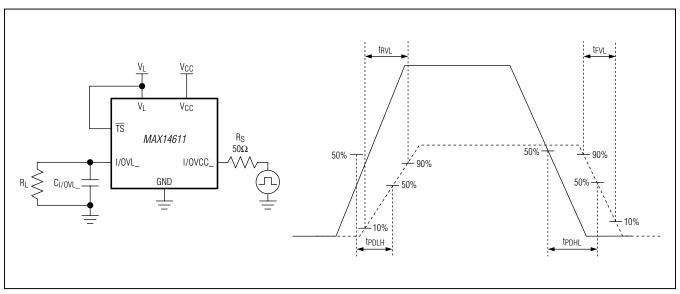


Figure 3. Push-Pull Driving I/OVCC_

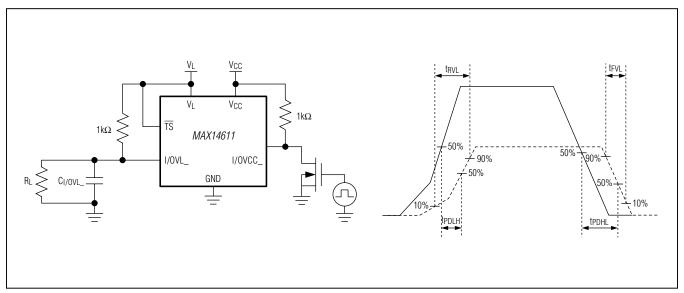
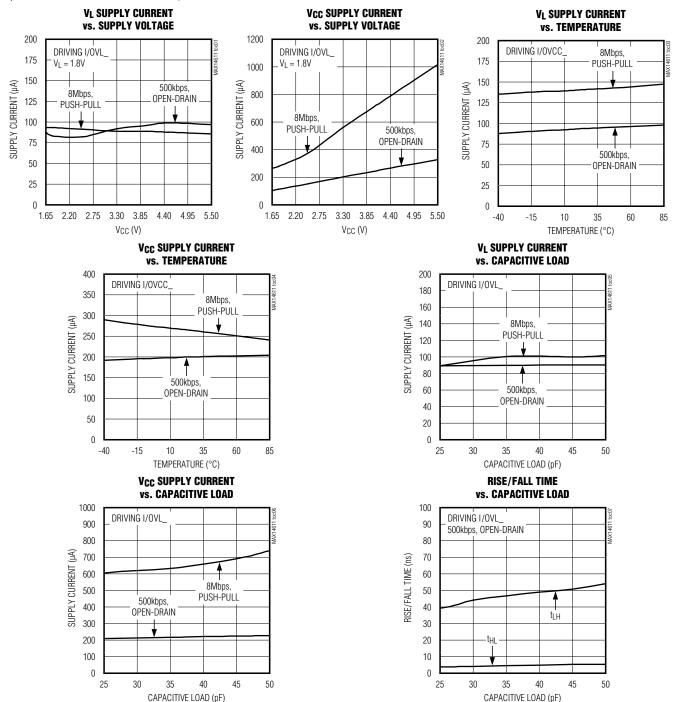


Figure 4. Open-Drain Driving I/OVCC_

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Typical Operating Characteristics

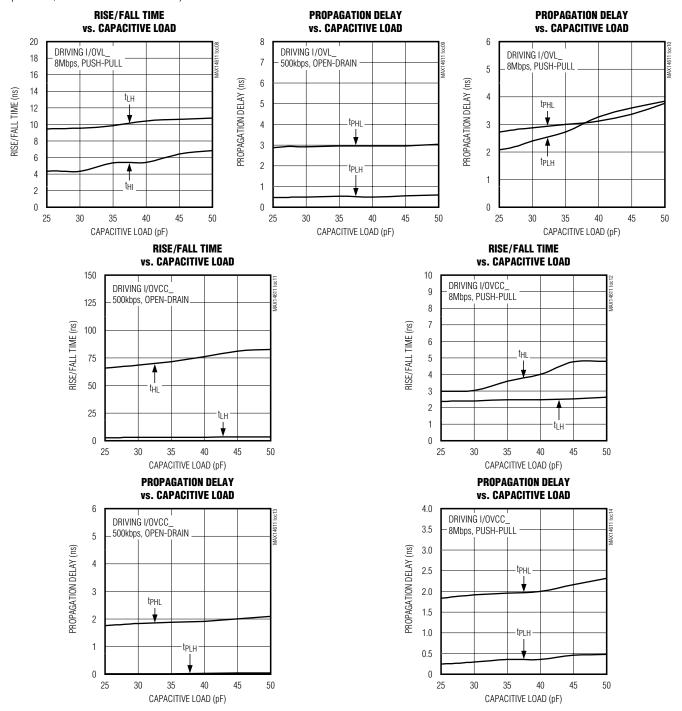
 $(V_{CC} = +3.3V, V_L = 1.8V, R_L = 1M\Omega, C_L = 15pF, T_A = +25^{\circ}C$, data rate = 500kbps in open-drain operation and 8Mbps in push-pull operation, unless otherwise noted.)



Quad Bidirectional Low-Voltage Logic-Level Translator

Typical Operating Characteristics (continued)

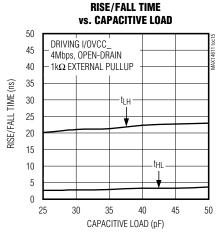
 $(V_{CC} = +3.3V, V_L = 1.8V, R_L = 1M\Omega, C_L = 15pF, T_A = +25^{\circ}C$, data rate = 500kbps in open-drain operation and 8Mbps in push-pull operation, unless otherwise noted.)



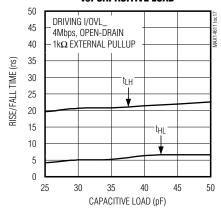
Quad Bidirectional Low-Voltage Logic-Level Translator

Typical Operating Characteristics (continued)

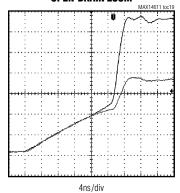
 $(V_{CC} = +3.3V, V_L = 1.8V, R_L = 1M\Omega, C_L = 15pF, T_A = +25^{\circ}C$, data rate = 500kbps in open-drain operation and 8Mbps in push-pull operation, unless otherwise noted.)



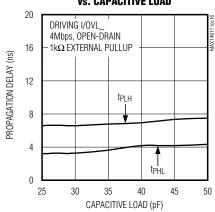
RISE/FALL TIME vs. CAPACITIVE LOAD



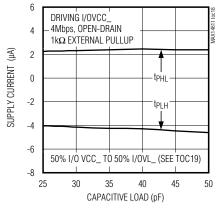
LOW-TO-HIGH TRANSITION, OPEN-DRAIN ZOOM



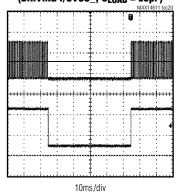
PROPAGATION DELAY vs. CAPACITIVE LOAD



PROPAGATION DELAY vs. CAPACITIVE LOAD

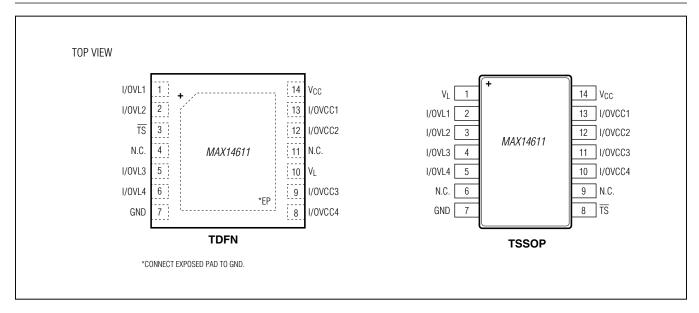


ENTERING AND EXITING THREE-STATE MODE (DRIVING I/OVCC_, CLOAD = 50pF)



Quad Bidirectional Low-Voltage Logic-Level Translator

Pin Configurations

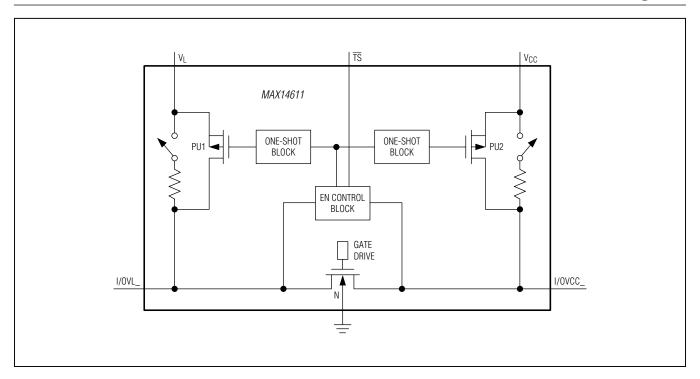


Pin Description

PI	PIN		FUNCTION		
TDFN-EP	TSSOP	NAIVIE	FUNCTION		
1	2	I/OVL1	Input/Output 1. Reference to V _L .		
2	3	I/OVL2	Input/Output 2. Reference to V _L .		
3	8	TS	Three-State Select Input. Drive $\overline{\text{TS}}$ low to place the device in three-state output mode. I/OVCC_ and I/OVL_ are high impedance in three-state output mode. Note: Logic referenced to V _L (for logic thresholds, see the <i>Electrical Characteristics</i> table).		
4, 11	6,9	N.C.	No Connection. Not internally connected.		
5	4	I/OVL3	Input/Output 3. Reference to V _L .		
6	5	I/OVL4	Input/Output 4. Reference to V _L .		
7	7	GND	Ground		
8	10	I/OVCC4	Input/Output 4. Reference to V _{CC} .		
9	11	I/OVCC3	Input/Output 3. Reference to V _{CC} .		
10	1	VL	Logic Supply Voltage Input, $0.9V \le V_L \le \min (5.0V, (V_{CC} + 0.3V))$. Connect a $0.1\mu F$ ceramic capacitor as close as possible to the pin.		
12	12	I/OVCC2	Input/Output 2. Reference to V _{CC} .		
13	13	I/OVCC1	Input/Output 1. Reference to V _{CC} .		
14	14	V _{CC}	Power Supply Input. The supply range is $1.65 \text{V} \le \text{V}_{\text{CC}} \le 5.5 \text{V}$. Bypass V_{CC} with a 1µF ceramic capacitor as close as possible to the pin to achieve higher ESD protection (±6kV HBM).		
_	_	EP	Exposed Pad (TDFN Only). EP is internally connected to GND. Connect to a large ground plane to maximize thermal performance. Not intended as an electrical connection point.		

Quad Bidirectional Low-Voltage Logic-Level Translator

Functional Diagram



Detailed Description

The MAX14611 ESD-protected level translator provides the level shifting necessary to allow data transfer in a multivoltage system. Externally applied voltages, V_{CC} and V_{L} , set the logic levels on either side of the device. A low-voltage logic signal present on the V_{L} side of the device appears as a high-voltage logic signal on the V_{CC} side of the device, and vice-versa.

The MAX14611 bidirectional level translator utilizes a transmission-gate based design (see the *Functional Diagram*) to allow data translation in either direction (V_L V_{CC}) on any single data line. The device accepts V_L from +0.9V to +5.0V and V_{CC} from +1.65V to +5.5V, making it ideal for data transfer between low-voltage ASICs/PLDs and higher voltage systems.

The device features a three-state output mode, thermal short-circuit protection, and $\pm 6 \text{kV}$ ESD protection on the V_{CC} side for greater protection in applications that route signals externally.

Level Translation

For proper operation, ensure that +1.65V \leq V_{CC} \leq +5.5V, 0.9V \leq V_L \leq 5.0V, and V_L \leq (V_{CC} + 0.3V). It is permissible for V_L to exceed (V_{CC} + 0.3V) during power-up sequencing. During power-supply sequencing, when V_{CC} is disconnected and V_L is powered up, a current can be sourced without a latchup or any damage to the device. The maximum data rate of the MAX14611 depends heavily on load capacitance (see the *Typical Operating Characteristics*), output impedance of the driver, and the operational voltage (see the *Timing Characteristics* table).

Speed-Up Circuitry

The device features a one-shot generator that decreases the rise time of the output. When triggered following a rising edge, MOSFETs PU1 and PU2 turn on for a short time to pull up I/OVL_ and I/OVCC_ to their respective supplies (see the *Functional Diagram*). This greatly reduces the rise time and propagation delay for the low-to-high transition.

Quad Bidirectional Low-Voltage Logic-Level Translator

Rise-Time Accelerators (Figure 5)

The device has internal rise-time accelerators, allowing operation up to 20Mbps. The rise-time accelerators are present on both sides of the device and act to speed up the rise time of the input and output of the device, regardless of the direction of the data. The triggering mechanism for these accelerators is both level and edge sensitive. To prevent false triggering of the rise-time accelerators, and to take full advantage of them, signal rise/fall times of less than 2ns/V are recommended for both sides of the device. In open-drain driving, the recommendation only applies for fall time. Under less noisy conditions, longer signal fall times can be acceptable.

Three-State Output Mode (\overline{TS})

Drive $\overline{\text{TS}}$ low to place the device in three-state output mode. Connect $\overline{\text{TS}}$ to V_L (logic-high) for normal operation. Activating the three-state output mode disconnects the internal 10k Ω pullup resistors on the I/OVCC_ and I/OVL_ lines. This forces the I/O lines to a high-impedance state and decreases the supply current to less than 1µA. The high-impedance I/O lines in three-state output mode allow for use in a multidrop network. When in three-state output mode, keep the I/OVL_ voltage below (V_L + 0.3V), and keep the I/OVCC_ voltage below (V_{CC} + 0.3V).

Thermal Short-Circuit Protection

Thermal-overload detection protects the device from short-circuit fault conditions. In the event of a short-circuit fault and when the junction temperature (T_J) reaches +150°C (typ), a thermal sensor signals the three-state output mode logic to force the device into three-state output mode. When T_J has cooled to +130°C (typ), normal operation resumes.

High ESD Protection

As with all Maxim devices, ESD-protection structures are incorporated on all pins to protect against electrostatic

discharges encountered during handling and assembly. The I/OVCC_ lines have extra protection against static electricity. Maxim's engineers have developed state-of-the-art structures to protect these pins against ESD of ±6kV without damage.

The ESD structures withstand high ESD in all states: normal operation, three-state output mode, and powered down. After an ESD event, the device keeps working without latchup, whereas competing products can latch and must be powered down to remove latchup. ESD protection can be tested in various ways. The I/OVCC_ lines of this product family are characterized for protection.to ±6kV using the Human Body Model.

ESD Test Conditions

Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

Applications Information

Power-Supply Decoupling

Bypass V_L to ground with a 0.1 μ F capacitor to reduce ripple and ensure correct data transmission. See the *Typical Operating Circuit*. To ensure full ±6kV ESD protection, bypass V_{CC} to ground with a 1 μ F capacitor. Place all capacitors as close as possible to the power-supply pins (V_{CC} and V_L).

Push-Pull vs. Open-Drain Driving

The device can be driven in a push-pull configuration. The device includes internal $10k\Omega$ resistors that pull up I/OVL_ and I/OVCC_ to their respective power supplies, allowing operation of the I/O lines with open-drain devices. See the <code>Timing Characteristics</code> table for maximum data rates when using open-drain drivers (<code>Figure 1</code>, <code>Figure 2</code>, <code>Figure 3</code>, <code>Figure 4</code>).

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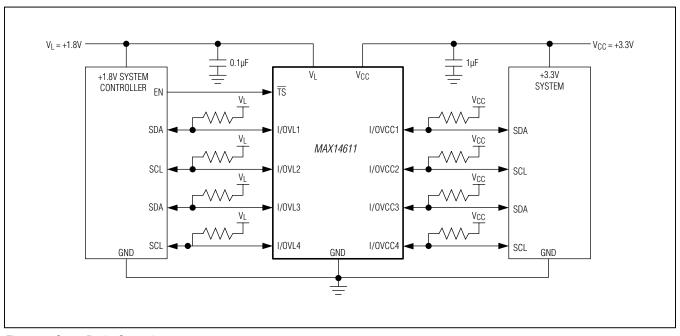
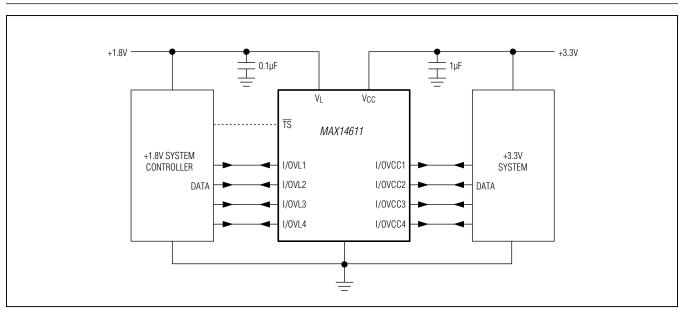


Figure 5. Open-Drain Operation

Applications Circuit



Package Information

Quad Bidirectional Low-Voltage Logic-Level Translator

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX14611ETD+	-40°C to +85°C	14 TDFN-EP*
MAX14611EUD+**	-40°C to +85°C	14 TSSOP

⁺Denotes a lead(Pb)-free/RoHS-compliant package.

PROCESS: BICMOS

Chip Information

For the latest package outline information and land patterns (foot-

For the latest package outline information and land patterns (footprints), go to www.maximintegrated.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	OUTLINE NO.	LAND PATTERN NO.
14 TDFN-EP	T1433+2	<u>21-0137</u>	90-0063
14 TSSOP	U14+1	21-0066	90-0113

^{*}EP = Exposed pad.

^{**}Future product—contact factory for availability.

Quad Bidirectional Low-Voltage Logic-Level Translator

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	4/12	Initial release	_



Maxim Integrated cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim Integrated product. No circuit patent licenses are implied. Maxim Integrated reserves the right to change the circuitry and specifications without notice at any time. The parametric values (min and max limits) shown in the Electrical Characteristics table are guaranteed. Other parametric values quoted in this data sheet are provided for guidance.

X-ON Electronics

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NLSX5011MUTCG NLV9306USG NLVSX4014MUTAG NLSV4T3144MUTAG NLVSX4373MUTAG NB3U23CMNTAG
MAX3371ELT+T NLSX3013BFCT1G NLV7WBD3125USG NLSX3012DMR2G 74AVCH1T45FZ4-7 NLVSV1T244MUTBG
74AVC1T45GS-Q100H CLVC16T245MDGGREP MC10H124FNG CAVCB164245MDGGREP CD40109BPWR MC10H350FNG
MC10H125FNG MC100EPT21MNR4G MC100EP91DWG NLSX3018MUTAG NLSV2T244MUTAG NLSX3013FCT1G
NLSX5011AMX1TCG PCA9306USG SN74GTL1655DGGR SN74AVCA406LZQSR NLSX4014DTR2G NLSX3018DTR2G
LTC1045CSW#PBF LTC1045CN#PBF SY100EL92ZG 74AXP1T34GMH 74AXP1T34GNH LSF0204DPWR PI4ULS3V204LE
ADG3245BRUZ-REEL7 ADG3123BRUZ ADG3245BRUZ ADG3246BCPZ ADG3308BCPZ-REEL ADG3233BRJZ-REEL7
ADG32233BRMZ